

光鋇科技股份有限公司
Epileds Technologies, Inc.
 Product specification of 45 x45 mil blue LED chip.

1. Scope:

This specification applies to InGaN/GaN 45 x 45mil blue LED chip, EP-B4545K-A3 ◦

2. Materials :

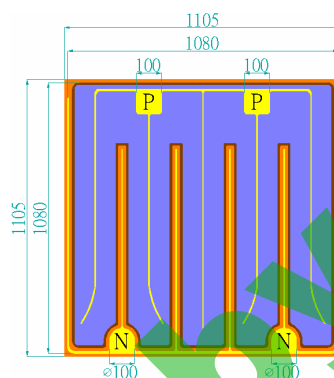
2.1 P-contact : Conductive Layer ◦

2.2 P-pad : Au ◦

2.3 N-pad : Au ◦

2.4 Backside Metal:

EP-B4545K -A3 : Reflective Layer (Al) with Au



3. Dimensions :

3.1 Chip size : 1140±30μm x 1140±30μm ◦

3.2 P-pad : φ100±10μm, thickness 2±0.2μm ◦

3.3 N-pad : φ100±10μm, thickness 2±0.2μm ◦

3.4 Chip thickness : 150μm±10μm ◦

4. Electro-optical characteristics and specification: (Tc=25°C)

4.1 Electro-optical characteristics

Test parameter	Condition	Min	Typ	Max	Unit
Dominant wavelength(Wd)	350mA	445	-	475	nm
Radiant intensity(I)	350mA	240	-	560	mW/sr
Forward voltage(Vf4)	10uA	1.9	-	2.5	V
Forward voltage(Vf1)	350mA	2.8	-	3.8	V
Reverse current (Ir)	-5V	0	-	2	uA

4.2 Electro-optical specification(Bin table) :

Wd		I		Vf4 (V)	Vf1 (V)	Ir (uA)
Bin	nm	Bin	mW/sr			
PS	445~447.5	17	240~255	1.9~2.5	2.8~3.8	0~2
PT	447.5~450	50	255~270			
BA	450~452.5	51	270~285			
BB	452.5~455	52	285~300			
BC	455~457.5	53	300~325			
BD	457.5~460	54	325~350			
BE	460~462.5	55	350~380			
BF	462.5~465	56	380~410			
BG	465~467.5	57	410~440			
BH	467.5~470	58	440~480			
BI	470~472.5	59	480~520			
BJ	472.5~475	60	520~560			

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* The detail technical and reliability datasheet are also available for your reference, please be free to contact us.

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